## AMENDMENTS TO THE CLAIMS

The claims in this listing will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

Claim 1. (Currently Amended) A light-emitting device formed by depositing p-type and n-type nitride semiconductor layers, comprising:

deposited p-type an n-type nitride semiconductor layers;

semiconductor-surface-electrodes to apply currents into each of the semiconductor layers;

an insulating layer which holds the semiconductor layers, said insulating layer comprising two surfaces; and

mount-surface-electrodes provided on one surface of the insulating layer which is opposite to the other surface of the insulating layer where the semiconductor-surface-electrodes are made;

wherein one of the semiconductor layers has a non-deposited area where the other semiconductor layer is not deposited;

one of the semiconductor-surface-electrodes is built up on the surface of the non-deposited area;

vias are made in the insulating layer which electrically connect the semiconductor-surface-electrodes and the mount-surface-electrodes;

the semiconductor-surface-electrodes, the insulating layer, and the mount-surface-electrodes are built up in this order on one side of the deposited semiconductor layers; and

~~the other~~ a surface of the other side of the deposited semiconductor layers is ~~used as~~ a light emitting surface ~~and there are no obstacles including obstacles comprising a sapphire substrate or electrodes on the surface~~ which is not covered by transparent crystal substrate.

Claim 2. (Original) The light-emitting device of claim 1, wherein the insulating layer is made of one of resin, ceramics, or silicon.

Claim 3. (Previously Presented) The light-emitting device of claim 1, wherein the vias are filled with electric conductor.

Claim 4. (Previously Presented) The light-emitting device of claim 1, wherein phosphor is provided on a surface or in an interior portion of the semiconductor layer.

Claim 5. – Claim 18. (Canceled)